



Session Title:	[WC1] Functional Wet Etching Technology
Session Date:	November 22 (Wed.), 2023
Session Time:	08:30-10:10
Session Room:	Room C (Grand Ballroom 2, 2F)
Session Chair:	Prof. Jea-Gun Park (Hanyang Univ., Korea)

[WC1-1] [Invited]

08:30-09:00

Enhancing Planarity and Defect Management in Chemical Mechanical Planarization (CMP) Slurry for Advanced Middle-of-Line (MOL) Semiconductor Processes

Ungyu Paik, Taeseup Song, Ganggyu Lee, Sungmin Kim, Donghwan Kim, Myungju Woo, Yeram Lee, Hongjun Park, Bobae Lee (Hanyang Univ., Korea), Yehwan Kim, and Samjong Choi (Samsung Electronics Co., Ltd., Korea)

[WC1-2]

09:00-09:20

Novel Wet Oxidant for Highly Selective Etching of $\text{Si}_{0.7}\text{Ge}_{0.3}$ - to Si-film Using Hydroxyl Radical Oxidation

Chang-Jin Lee, Ji-Eun Lee, Eun-Woo Jang, and Jea-Gun Park (Hanyang Univ., Korea)

[WC1-3]

09:20-09:40

Enhancing Etch Rate Selectivity between $\text{Si}_{0.7}\text{Ge}_{0.3}$ - and Si-Film via Radical Concentration Control for Radical Oxidation-Based Wet Etchant

Ji-Eun Lee, Chang-Jin Lee, Eun-Woo Jang, and Jea-Gun Park (Hanyang Univ., Korea)

[WC1-4] [Invited]

09:40-10:10

Surface Preparation for InGaAs MOSFET Fabrication

Sangwoo Lim (Yonsei Univ., Korea)